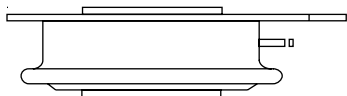


## Phase Control Thyristors (Hockey PUK Version), 350 A



TO-200AB (A-PUK)

### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (A-PUK)
- Lead (Pb)-free
- Designed and qualified for industrial level



**RoHS**  
COMPLIANT

### PRODUCT SUMMARY

$I_{T(AV)}$	350 A
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### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

### MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		350	A
	$T_{hs}$	55	°C
$I_{T(RMS)}$		660	A
	$T_{hs}$	25	°C
$I_{TSM}$	50 Hz	5000	A
	60 Hz	5230	
$I^2t$	50 Hz	125	kA <sup>2</sup> s
	60 Hz	114	
$V_{DRM}/V_{RRM}$		400 to 2000	V
$t_q$	Typical	100	μs
$T_J$		- 40 to 125	°C

### ELECTRICAL SPECIFICATIONS

#### VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST180C..C	04	400	500	30
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	I <sub>T(AV)</sub>	180° conduction, half sine wave double side (single side) cooled			350 (140)	A
					55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C heatsink temperature double side cooled			660	A
Maximum peak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	5000	
		t = 8.3 ms			5230	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied		4200	
		t = 8.3 ms			4400	
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	t = 10 ms	No voltage reapplied		125	
		t = 8.3 ms			114	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied	88		
		t = 8.3 ms		81		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no voltage reapplied			1250	kA <sup>2</sup> √s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % × π × I <sub>T(AV)</sub> ) < I < π × I <sub>T(AV)</sub> , T <sub>J</sub> = T <sub>J</sub> maximum			1.08	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	(I > π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			1.14	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % × π × I <sub>T(AV)</sub> ) < I < π × I <sub>T(AV)</sub> , T <sub>J</sub> = T <sub>J</sub> maximum			1.18	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	(I > π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			1.14	
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 750 A, T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> = 10 ms sine pulse			1.96	V
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			600	mA
Maximum (typical) latching current	I <sub>L</sub>				1000 (300)	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	$di/dt$	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage $\leq 80 \% V_{DRM}$	1000	A/μs
Typical delay time	$t_d$	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67 \% V_{DRM}$ , $T_J = 25$ °C	1.0	μs
Typical turn-off time	$t_q$	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $di/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs	100	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	$dV/dt$	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/μs
Maximum peak reverse and off-state leakage current	$I_{RRM}$ , $I_{DRM}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	30	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> ≤ 5 ms		10		W
Maximum average gate power	P <sub>G(AV)</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, f = 50 Hz, d% = 50		2.0		
Maximum peak positive gate current	I <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> ≤ 5 ms		3.0		A
Maximum peak positive gate voltage	+ V <sub>GM</sub>			20		V
Maximum peak negative gate voltage	- V <sub>GM</sub>			5.0		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		T <sub>J</sub> = 25 °C		90	150	
		T <sub>J</sub> = 125 °C		40	-	
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = - 40 °C		2.9	-	V
		T <sub>J</sub> = 25 °C		1.8	3.0	
		T <sub>J</sub> = 125 °C		1.2	-	
DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T <sub>J</sub>		- 40 to 125	°C
Maximum storage temperature range	T <sub>Stg</sub>		- 40 to 150	
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation single side cooled	0.17	K/W
		DC operation double side cooled	0.08	
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation single side cooled	0.033	
		DC operation double side cooled	0.017	
Mounting force, ± 10 %			4900 (500)	N (kg)
Approximate weight			50	g
Case style		See dimensions - link at the end of datasheet	TO-200AB (A-PUK)	

$\Delta R_{thJC}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.015	0.015	0.011	0.011	T <sub>J</sub> = T <sub>J</sub> maximum	K/W
120°	0.018	0.019	0.019	0.019		
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

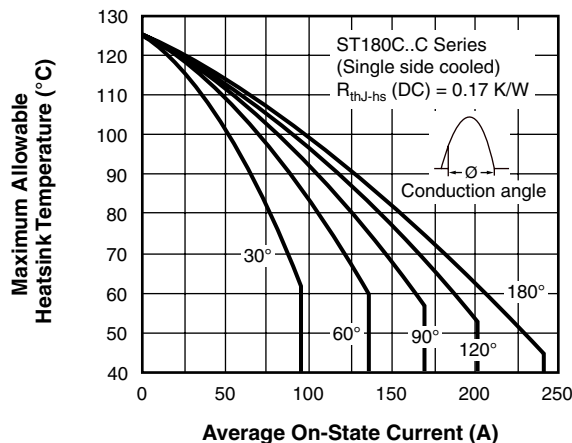


Fig. 1 - Current Ratings Characteristics

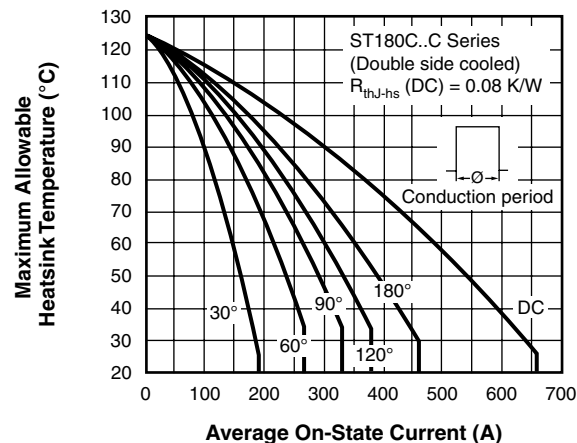


Fig. 4 - Current Ratings Characteristics

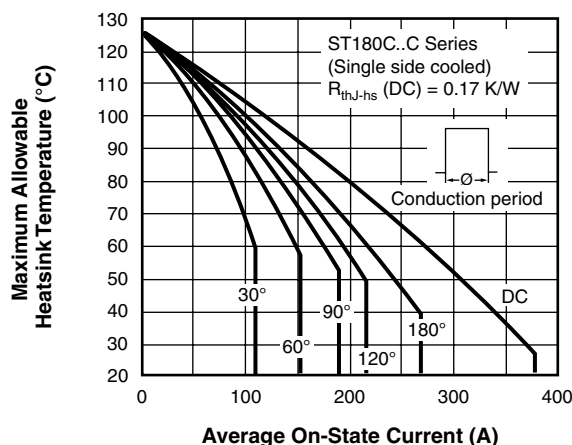


Fig. 2 - Current Ratings Characteristics

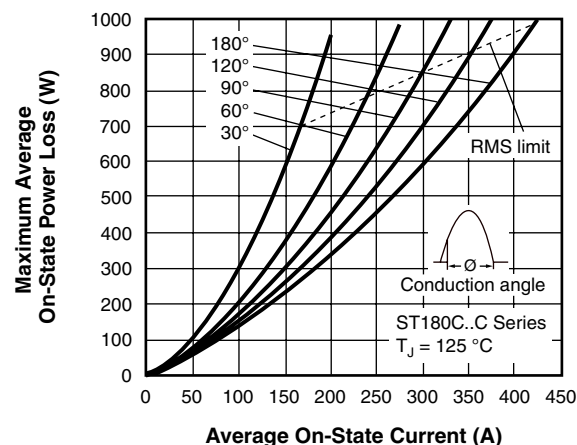


Fig. 5 - On-State Power Loss Characteristics

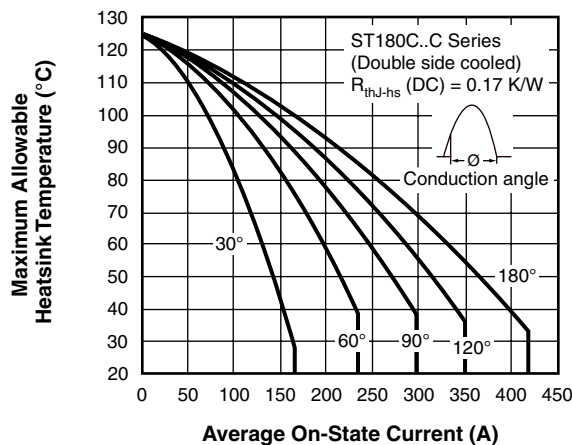


Fig. 3 - Current Ratings Characteristics

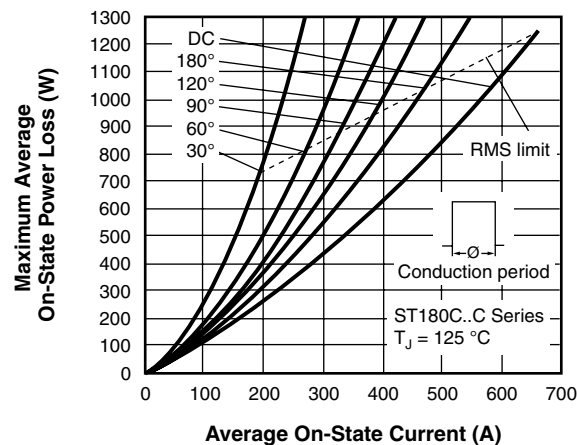


Fig. 6 - On-State Power Loss Characteristics

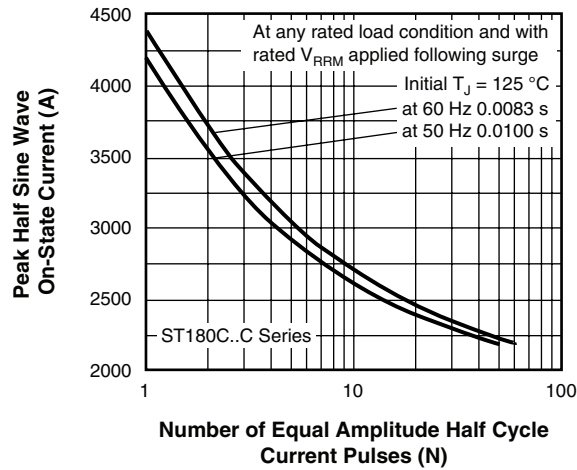


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

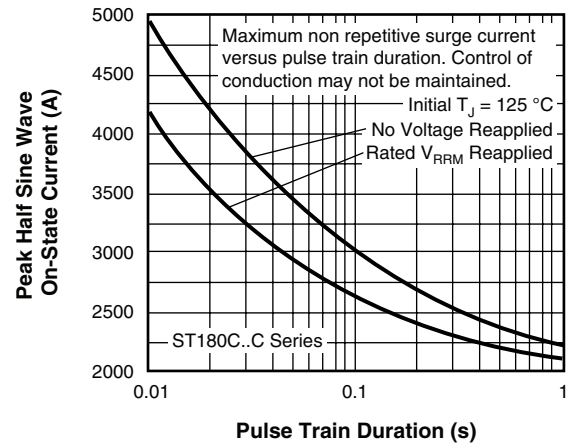


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

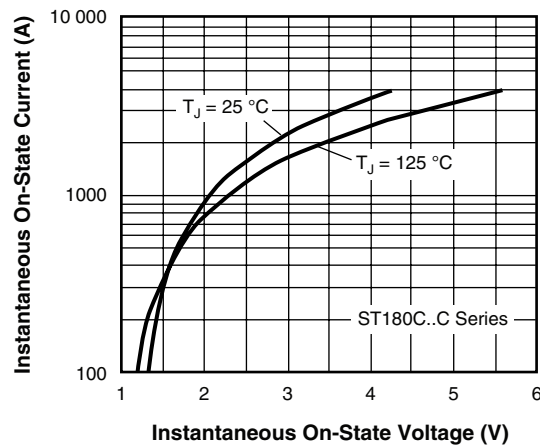


Fig. 9 - On-State Voltage Drop Characteristics

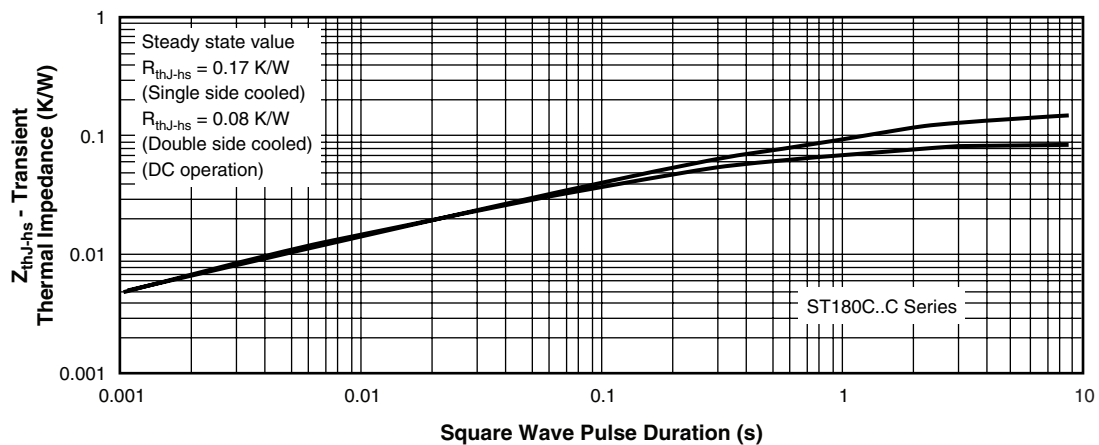


Fig. 10 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

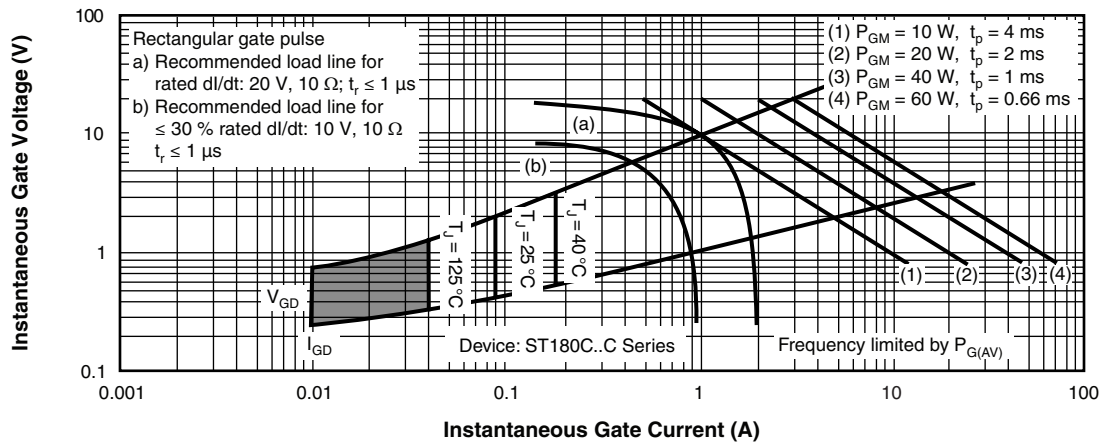


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	ST	18	0	C	20	C	1	-	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

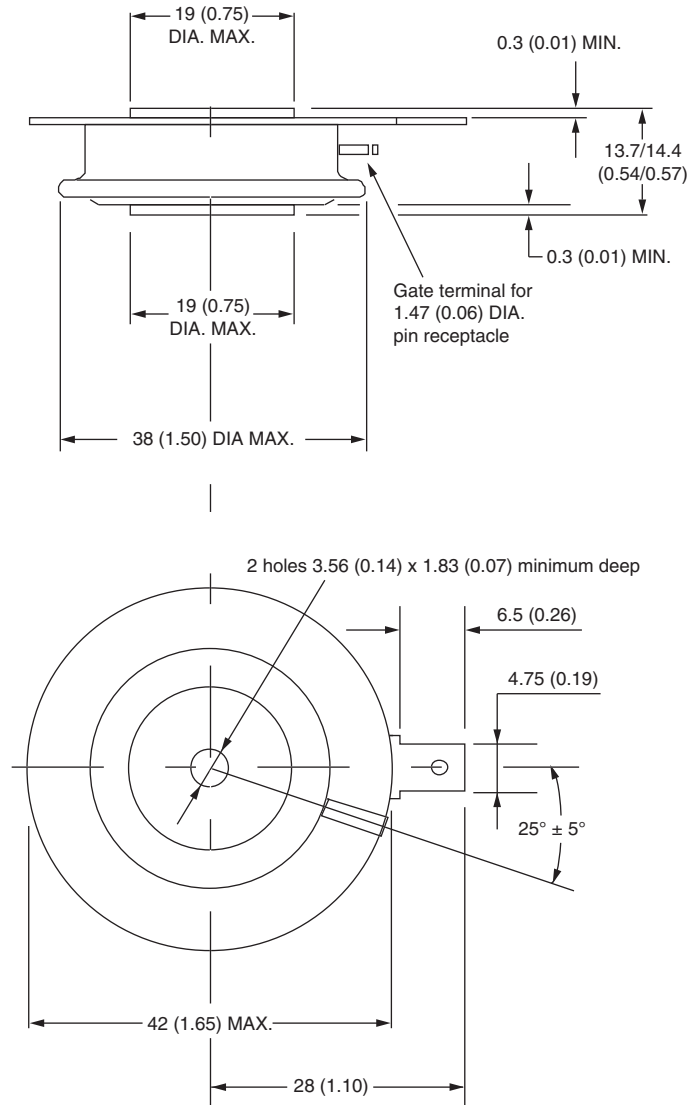
- ① - Thyristor
- ② - Essential part number
- ③ - 0 = Converter grade
- ④ - C = Ceramic PUK
- ⑤ - Voltage code  $\times 100 = V_{RRM}$  (see Voltage Ratings table)
- ⑥ - C = PUK case TO-200AB (A-PUK)
- ⑦ - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)  
1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)  
2 = Eyelet terminals (gate and auxiliary cathode soldered leads)  
3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- ⑧ - Critical  $dV/dt$ :
  - None = 500 V/ $\mu s$  (standard selection)
  - L = 1000 V/ $\mu s$  (special selection)
- ⑨ - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95074">http://www.vishay.com/doc?95074</a>

## TO-200AB (A-PUK)

### DIMENSIONS in millimeters (inches)

Anode to gate  
Creepage distance: 7.62 (0.30) minimum  
Strike distance: 7.12 (0.28) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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